

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company



N-Channel Silicon MOSFET **CPH3455** — General-Purpose Switching Device **Applications**

Features

- ON-resistance $R_{DS}(on)1=80m\Omega(typ.)$
- 4V drive
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		35	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		3	А
Drain Current (Pulse)	IDP	PW⊴10µs, duty cycle≤1%	12	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

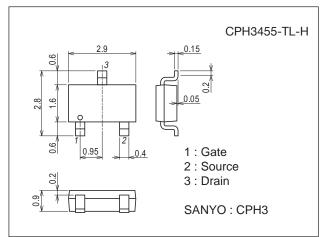
This product is designed to "ESD immunity < 200V*", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

7015A-004



Product & Package Information

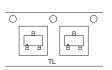
• Package

- JEITA, JEDEC
- : SC-59, TO-236, SOT-23

: CPH3

• Minimum Packing Quantity : 3,000 pcs./reel

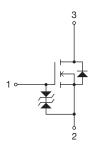
Packing Type: TL





Marking

Electrical Connection

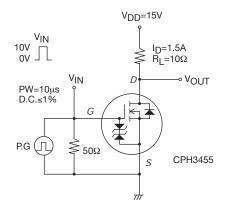


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Electrical Characteristics at Ta=25°C

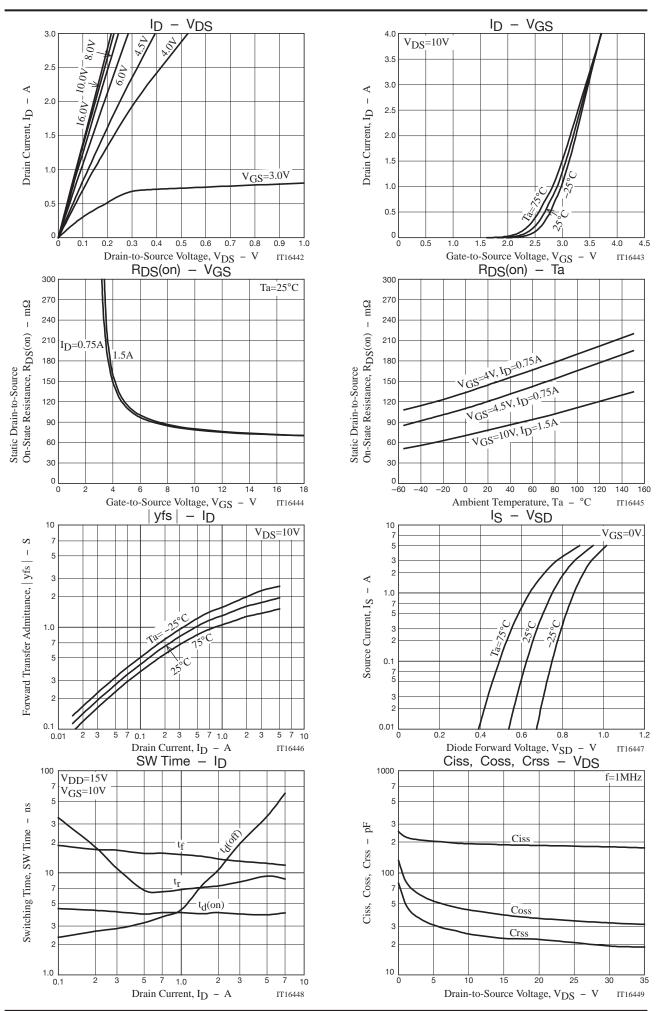
Parameter	O mark at	O a malifica ma		Ratings			
Parameter	Symbol	Conditions	min	typ max		- Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =35V, V _{GS} =0V			1	μA	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μA	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA 1.2			2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A		1.7		S	
	R _{DS} (on)1	ID=1.5A, VGS=10V		80	104	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	ID=0.75A, VGS=4.5V		123	173	mΩ	
	R _{DS} (on)3	I _D =0.75A, V _{GS} =4V		148	208	mΩ	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		186		pF	
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		36		pF	
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		22		pF	
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		4.2		ns	
Rise Time	tr	See specified Test Circuit.		4.7		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		15		ns	
Fall Time	tf	See specified Test Circuit.		5.7		ns	
Total Gate Charge	Qg	V _{DS} =20V, V _{GS} =10V, I _D =3A		4		nC	
Gate-to-Source Charge	Qgs	V _{DS} =20V, V _{GS} =10V, I _D =3A		0.9		nC	
Gate-to-Drain "Miller" Charge	Qgd	VDS=20V, VGS=10V, ID=3A		0.7		nC	
Diode Forward Voltage	VSD	IS=3A, VGS=0V		0.86	1.2	V	

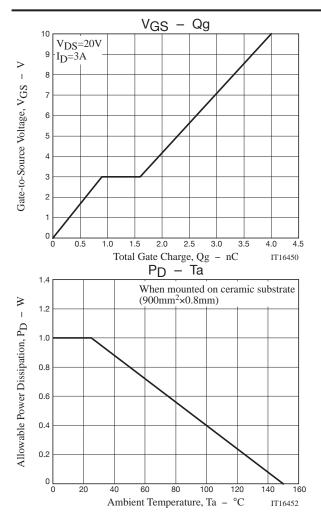
Switching Time Test Circuit

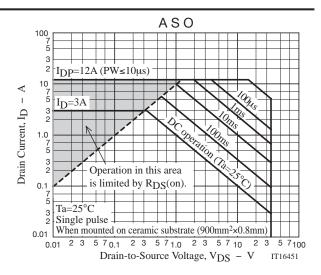


Ordering Information

Device Package		Shipping	memo		
CPH3455-TL-H	CPH3	3,000pcs./reel	Pb Free and Halogen Free		







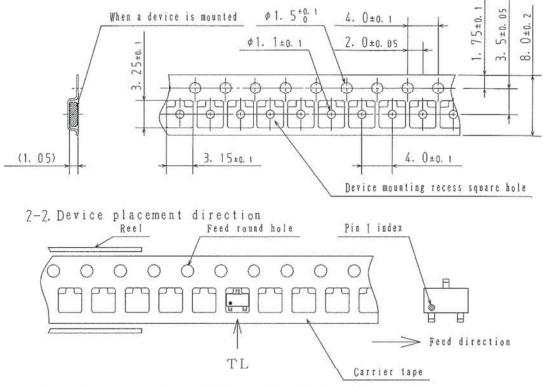
Embossed Taping Specification CPH3455-TL-H

1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format					
16-501-50-	Type			Outer box	Inner BOX (C-1)			Outer BOX (A-7)		
СРНЗ СРНЗ		3, 000 15, 00		90,000	5 reels contained Dimensions:mm(external)			6 inner boxes container Dimensions:mm (external		
					183	×72×	185	440×195×210		
Packing met	Type LOT Quan Orig Reel la	No. tity in		(U 1 077795 0000 11.	Inning in initial Inning in initial Inning in initial Inning in initial Inning initial Inninitial Inninitial Inning initial Inning initiali Inninitia	criptio rminal JEITA	IL The dis 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0			
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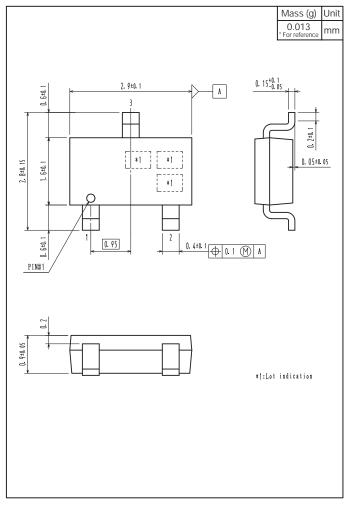
2. Taping configuration

2-1. Carrier tape size (unit:mm)

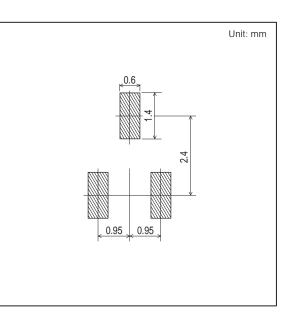


Those with one electrode terminal on the feed hole side TL

Outline Drawing CPH3455-TL-H



Land Pattern Example



Note on usage : Since the CPH3455 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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